L Number	Hits	Search Text	DB	Time stamp
1	126572		USPAT;	2004/02/08 16:45
		integrated adj circuit\$1) and (heat	US-PGPUB;	
		thermal\$2) near3 (sink\$3 absorb\$3	EPO; JPO	
		dissipat\$3 exchang\$3 remov\$3 transfer\$4)	•	
2	7795	((semiconductor\$1 chip\$1 die dice\$1 ic\$2	USPAT;	2004/02/08 16:47
		integrated adj circuit\$1) and (heat	US-PGPUB;	
		thermal\$2) near3 (sink\$3 absorb\$3	EPO; JPO	
		dissipat\$3 exchang\$3 remov\$3 transfer\$4))		
		and (heat thermal\$2) near3 (sink\$3		
		absorb\$3 dissipat\$3 exchang\$3 remov\$3		
		transfer\$4) same (carbon\$6 graphit\$2		
		diamon)		
3	1039	((semiconductor\$1 chip\$1 die dice\$1 ic\$2	USPAT;	2004/02/08 16:48
		integrated adj circuit\$1) and (heat	US-PGPUB;	
		thermal\$2) near3 (sink\$3 absorb\$3	EPO; JPO	
		<pre>dissipat\$3 exchang\$3 remov\$3 transfer\$4))</pre>		
	}	and solder\$3 same (carbon\$6 graphit\$2		
		diamond)		
4	34	((() = = = = = = = = = = = = = = = =	USPAT;	2004/02/08 16:48
		integrated adj circuit\$1) and (heat	US-PGPUB;	
		thermal\$2) near3 (sink\$3 absorb\$3	EPO; JPO	
		dissipat\$3 exchang\$3 remov\$3 transfer\$4))		
		and solder\$3 same (carbon\$6 graphit\$2		
		diamond)) and solder\$3 same (carbon\$6		
		graphit\$2 diamond) same (foam por\$3		
5	24	porosit\$3)	HODAM.	2004/02/02 17 52
5	34	((((semiconductor\$1 chip\$1 die dice\$1 ic\$2	USPAT;	2004/02/08 17:53
	ļ	integrated adj circuit\$1) and (heat thermal\$2) near3 (sink\$3 absorb\$3	US-PGPUB; EPO; JPO	
		dissipat\$3 exchang\$3 remov\$3 transfer\$4)	EPO; JPO	
		and solder\$3 same (carbon\$6 graphit\$2		
		diamond)) and solder\$3 same (carbon\$6		
		graphit\$2 diamond) same (foam por\$3		
		porosit\$3)) and solder\$3 same (carbon\$6		
		graphit\$2 diamond)		
6	0	("wo27776").PN.	USPAT;	2004/02/08 17:53
		, ,	US-PGPUB;	2001/02/00 17:55
			EPO; JPO	